

## EMBEDDED TIDBITS

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◆ **TSMC VERIFIES 0.15 $\mu$  MoSys MEMORY**

Taiwan Semiconductor Manufacturing Co. (TSMC) has successfully produced MoSys 1T-SRAM in its new 0.15-micron logic process, only three months after producing MoSys test chips in its 0.18-micron process. This will allow TSMC's customers to use MoSys memory in cutting-edge

system-on-a-chip designs. MoSys' 1T-SRAM technology essentially combines the advantages of DRAM and SRAM—it uses only one transistor per cell but doesn't need to be refreshed and has low access latencies (see [MPR 9/13/99-05](#), "MoSys Explains 1T-SRAM Technology"). For more information: [www.tsmc.com](http://www.tsmc.com) and [www.mosys.com](http://www.mosys.com). —T.R.H. ◆

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